

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. **(Currently Amended)** ~~A~~ An alkaline cleaning solution-surface treatment
~~operations in which metal impurity contamination becomes troublesome~~
comprising: an alkaline compound in an amount sufficient to render said solution
alkaline , hydrogen peroxide in a concentration of 0.3 to 22% by weight , water
and either 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris]
or 2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] and
nitrilotriacetic acid as chelating additive(s), for removing and inhibiting metal
contaminants from a semiconductor substrate surface in which metal impurity
contamination becomes troublesome.
2. **(Previously presented)** A cleaning solution according to claim 1, wherein the
alkaline compound is an organic base, ammonia, ammonium hydroxide, or
tetramethyl ammonium hydroxide.
3. **(Previously presented)** A cleaning solution according to claim 1, wherein the
alkaline compound is ammonia or ammonium hydroxide.
4. **(Currently Amended)** A cleaning solution according to claim 1, comprising
2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] in an
amount in the range of 1000 to 3000 ppm.
5. **(Previously presented)** A cleaning solution according to claim 1, comprising
nitrilotriacetic acid [NTA; CAS 139-13-9] in an amount in the range of 100 to
2000 ppm.
6. **(Previously presented)** A cleaning solution according to claim 1, comprising
2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] and
nitrilotriacetic acid in a total amount less than 4000 ppm.
7. **(Previously presented)** A cleaning solution according to claim 1, comprising
2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] and
nitrilotriacetic acid in a total amount less than 2000 ppm.
8. **(Previously presented)** A method for cleaning a semiconductor substrate
comprising treating the semiconductor substrate with a cleaning solution
according to claim 1, and drying said semiconductor substrate after water rinsing.

9. **(Previously presented)** A method of treatment according to claim 8, wherein the treatment with cleaning solution is carried out at a temperature the range of 20 to 80 °C.
10. **(Previously presented)** A method of treatment according to claim 8, wherein the treatment with cleaning solution is carried out at normal room temperature.
11. **(Previously presented)** A method of treatment according to claim 8, wherein said cleaning solution is brought into contact with a surface to be cleaned for a few seconds to 60 minutes.
12. **(Previously presented)** A method of treatment according to claim 8, wherein said cleaning solution is brought into contact with a surface to be cleaned for about 15 seconds to 15 minutes.
13. **(Previously presented)** A method for treatment of a semiconductor substrate according to claim 8, wherein the semi-conductor substrate is immersed / dipped in the cleaning solution.
14. **(Previously presented)** A method for surface treatment operations including cleaning, etching, polishing, film-forming, for the cleaning of substrates such as semiconductor, metal, glass, ceramics, plastic, magnetic material, superconductors comprising contacting said surface with a cleaning solution according to claim 1.
15. **(New)** A combination comprising:
 - a) a semiconductor substrate having a surface and
 - b) an alkaline cleaning solution comprising an alkaline compound, hydrogen peroxide in a concentration of 0.3 to 22% by weight , water
and
2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris] or
2,2-Bis-(hydroxyethyl)-(iminotris)-(hydroxymethyl)methane [Bis Tris]
and nitrilotriacetic acid as chelating additive(s),

wherein said cleaning solution is capable of removing and inhibiting metal contamination on the surface of said semiconductor substrate.